

TC74ACT521P, TC74ACT521F, TC74ACT521FW

8-BIT EQUALITY COMPARATOR

The TC74ACT521 is an advanced high speed CMOS 8-BIT DIGITAL COMPARATOR fabricated with silicon gate and double-layer metal wiring C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

It compares two 8-bit binary or BCD words applied inputs P₀~P₇, and inputs Q₀~Q₇, and indicates whether or not they are equal.

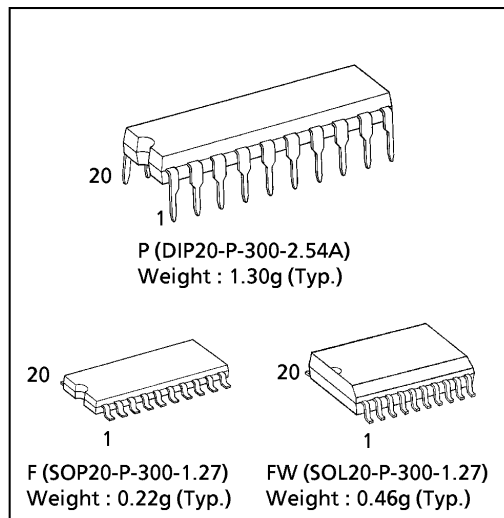
A signal active low enable is provided to facilitate cascading of several packages to compare of words greater than 8 bits.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

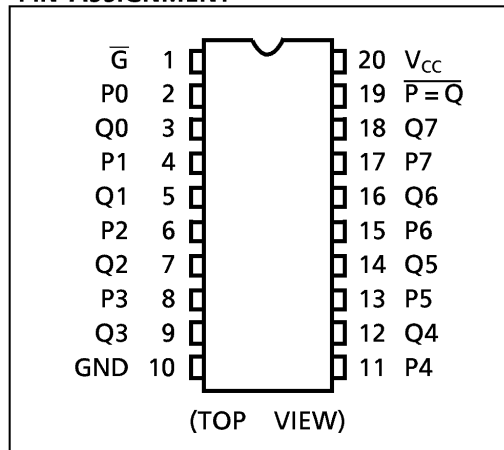
FEATURES :

- High Speed..... $t_{pd} = 6.4ns(typ.)$ at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 8\mu A(Max.)$ at $T_a = 25^\circ C$
- Compatible with TTL outputs..... $V_{IL} = 0.8V (Max.)$
 $V_{IH} = 2.0V (Min.)$
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 24mA (Min.)$
Capability of driving 50 Ω transmission lines.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Pin and Function Compatible with 74F521

(Note) The JEDEC SOP (FW) is not available in Japan.



PIN ASSIGNMENT



TRUTH TABLE

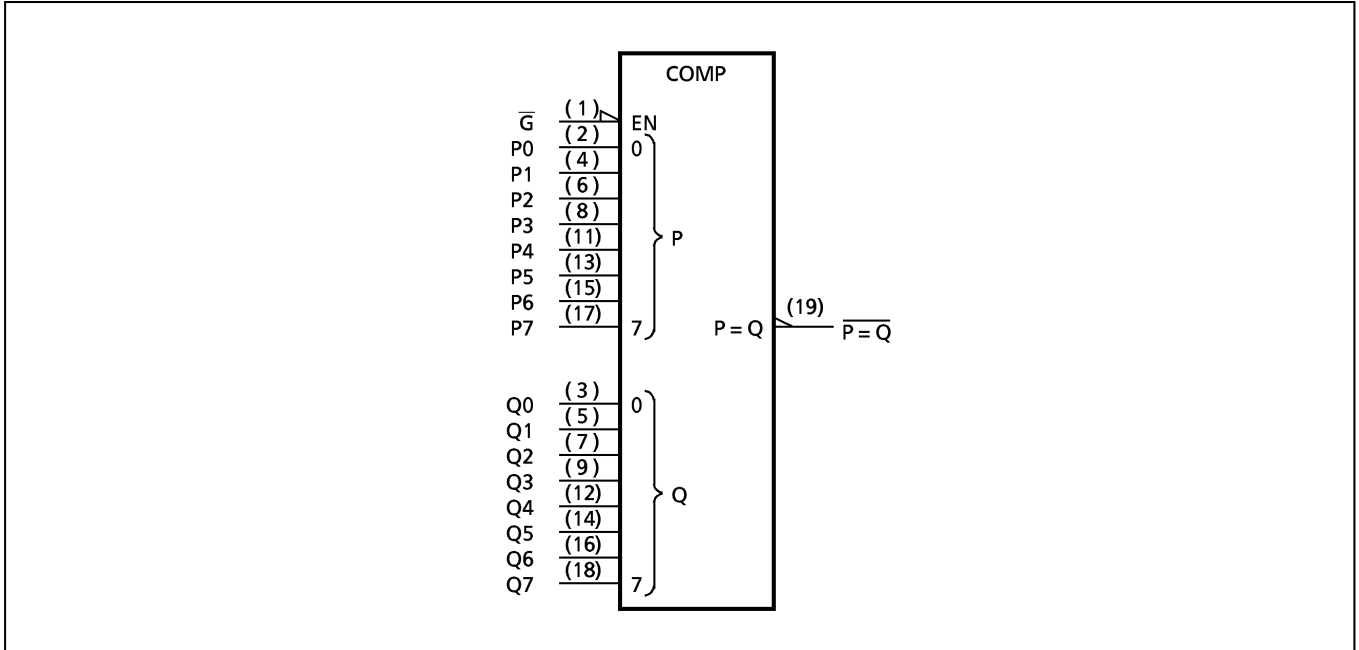
INPUTS		OUTPUT
P, Q	\overline{G}	$\overline{P=Q}$
P = Q	L	L
P \neq Q	L	H
X	H	H

X : Don't Care

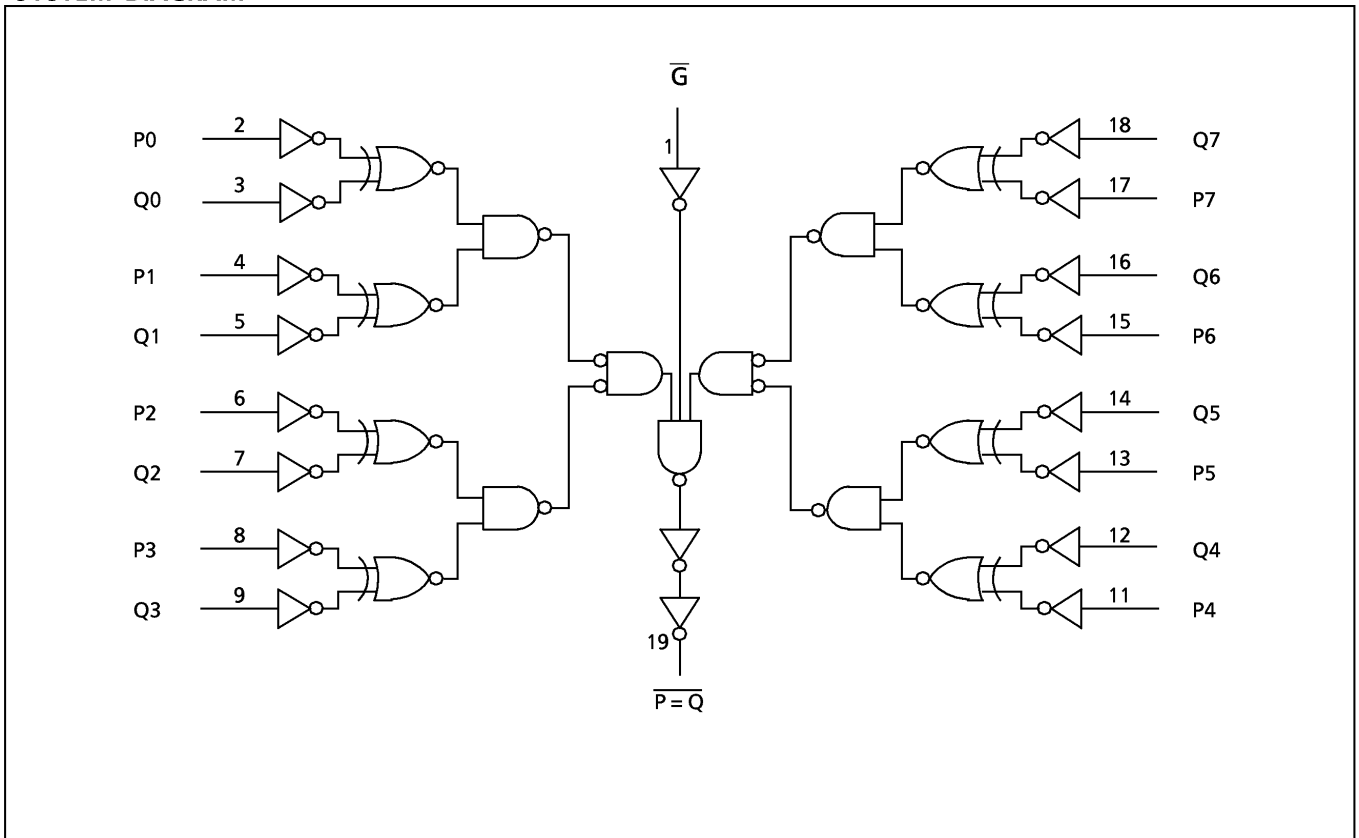
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IEC LOGIC SYMBOL



SYSTEM DIAGRAM



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 100	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	4.5~5.5	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	dt / dV	0~10	ns / V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		4.5 } 5.5	2.0	—	—	2.0	—	V	
Low - Level Input Voltage	V_{IL}		4.5 } 5.5	—	—	0.8	—	0.8	V	
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50\mu\text{A}$	4.5	4.4	4.5	—	4.4	—	V
			$I_{OH} = -24\text{mA}$	4.5	3.94	—	—	3.80	—	
			$I_{OH} = -75\text{mA}^*$	5.5	—	—	—	3.85	—	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50\mu\text{A}$	4.5	—	0.0	0.1	—	0.1	V
			$I_{OL} = 24\text{mA}$	4.5	—	—	0.36	—	0.44	
			$I_{OL} = 75\text{mA}^*$	5.5	—	—	—	—	1.65	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	± 0.1	—	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	8.0	—	80.0		
		I_C	PER INPUT : $V_{IN} = 3.4\text{V}$ OTHER INPUT : V_{CC} or GND	5.5	—	—	1.35	—	1.5	mA

* : This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, $R_L = 500\Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time (Pn, Qn - $\overline{P=Q}$)	t _{pLH} t _{pHL}		5.0 ± 0.5	—	7.1	11.4	1.0	13.0	ns
Propagation Delay Time ($\overline{G - P=Q}$)	t _{pLH} t _{pHL}		5.0 ± 0.5	—	5.7	8.3	1.0	9.5	
Input Capacitance	C _{IN}		—	5	10	—	10	pF	
Power Dissipation Capacitance	C _{PD} (1)		—	29	—	—	—		

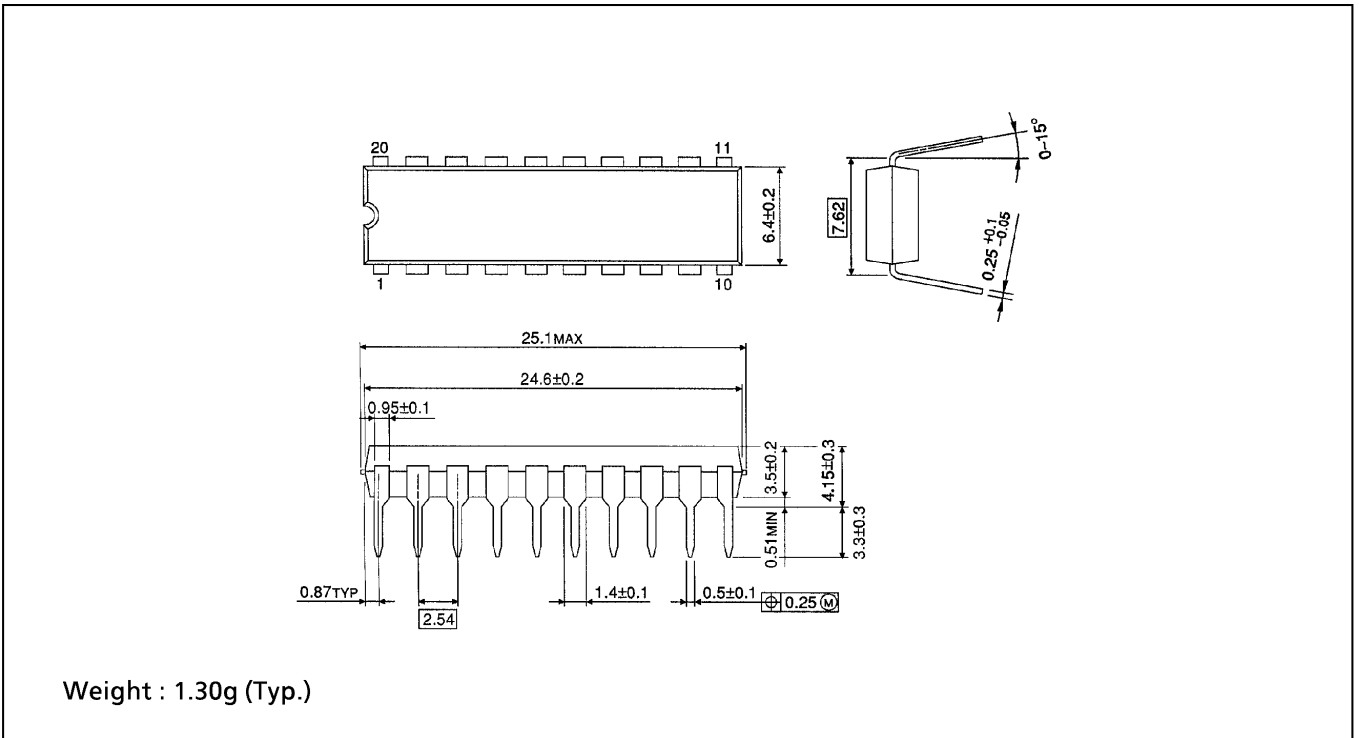
Note(1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

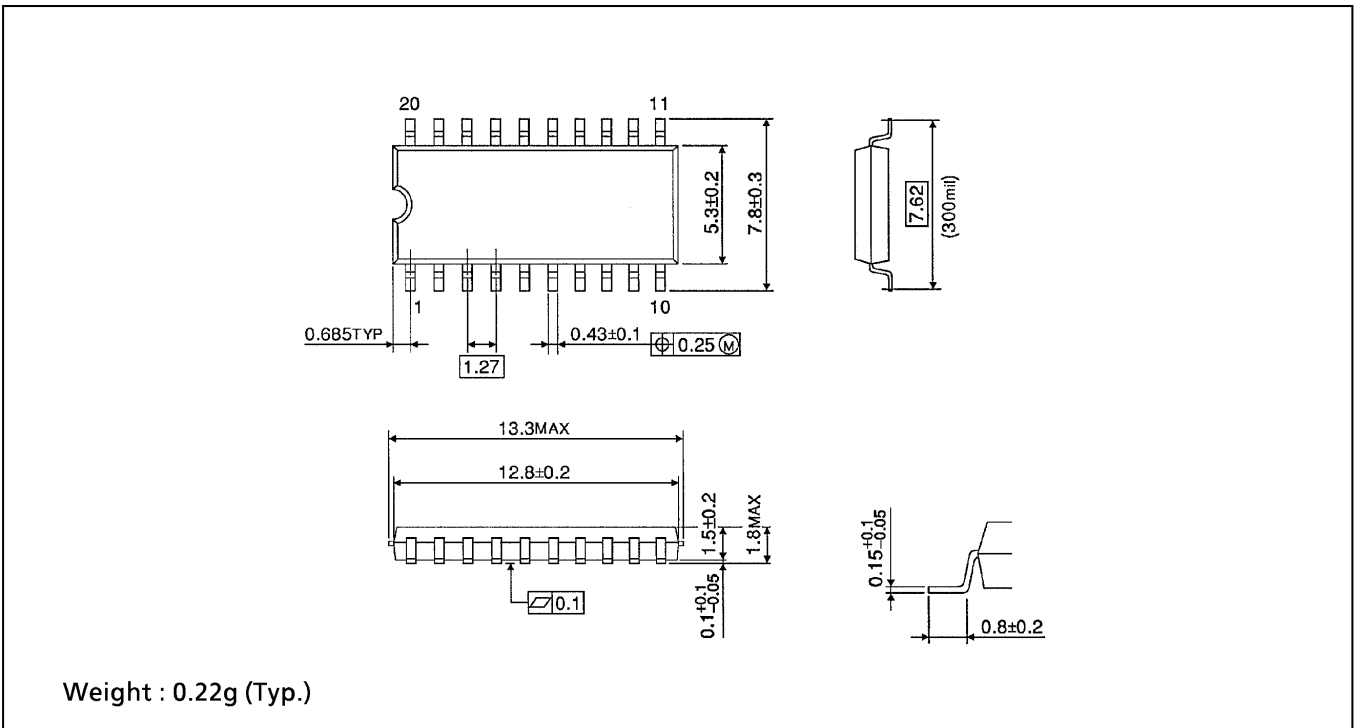
DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

Unit in mm



SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

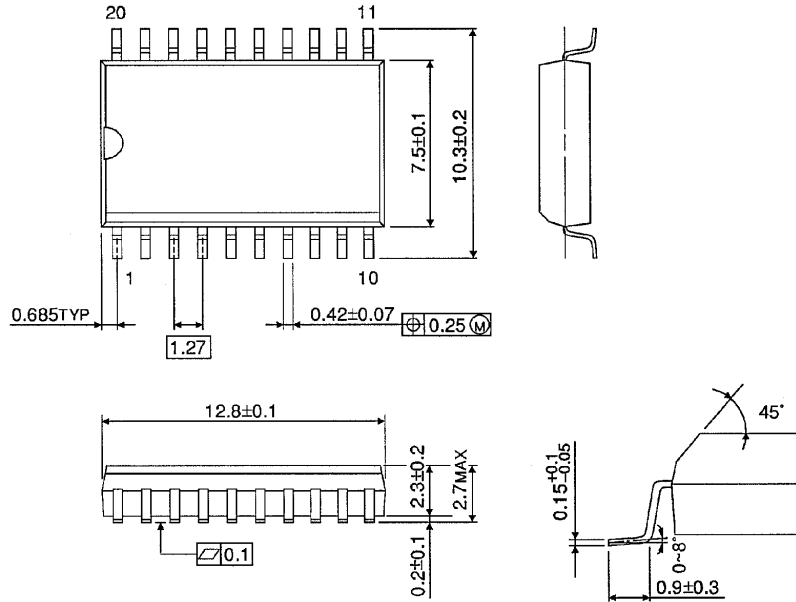
Unit in mm



SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)